IN THE CLAIMS:

Please add new claims 23-27, and amend the claims as follows:

1. (Currently Amended) A photomask etch chamber, comprising:

a substrate support member disposed inside the chamber, wherein the substrate support member is configured to support a photomask substrate;

a ceiling disposed on the chamber; and

an endpoint detection system configured to detect one or more test patterns disposed on a peripheral region of the photomask substrate.

2. (Original) The chamber of claim 1, wherein the endpoint detection system is disposed through a peripheral region of the ceiling and positioned directly above the peripheral region of the photomask substrate.

3. (Original) The chamber of claim 1, wherein the endpoint detection system is disposed through a peripheral region of the substrate support member and positioned directly below the peripheral region of the photomask substrate.

4. (Original) The chamber of claim 1, wherein the endpoint detection system is an interferometer endpoint detection system.

5. (Currently Amended) A photomask etch chamber, comprising:

a substrate support member disposed inside the chamber, wherein the substrate support member is configured to support a photomask substrate;

a ceiling disposed on the chamber; and

an interferometer endpoint detection system disposed through a peripheral region of the ceiling, wherein the interferometer endpoint detection system is configured to detect one or more test patterns disposed on a peripheral region of the photomask substrate.

6. (Original) The chamber of claim 5, wherein the interferometer endpoint detection system is disposed directly above a corner region of the photomask substrate.

7. (Original) The chamber of claim 5, wherein the photomask substrate is about 6 inches wide and about 6 inches long and the interferometer endpoint detection system is disposed about 2.8 inches from a horizontal center line and about 2.8 inches from a vertical center line of the photomask substrate.

8. (Original) The chamber of claim 5, wherein the interferometer endpoint detection system is disposed directly above a peripheral region of the photomask substrate.

9. (Original) The chamber of claim 5, wherein the interferometer endpoint detection system is configured to detect a peripheral region of the photomask substrate.

10. (Cancelled) The chamber of claim 5, wherein the interferometer endpoint detection system is configured to detect one or more test patterns disposed on a peripheral region of the photomask substrate.

11. (Original) The chamber of claim 5, wherein the interferometer endpoint detection system is configured to detect one or more test patterns disposed on a corner region of the photomask substrate.

12. (Original) The chamber of claim 5, wherein the interferometer endpoint detection system comprises:

a light source for sending a light beam to a surface of the substrate; and

a light detector for measuring the intensity of the light beam reflected from the substrate surface.

13. (Original) The chamber of claim 5, wherein the interferometer endpoint detection system further comprises a focusing assembly for focusing the light beam to a spot on the substrate surface.

14. (Original) The chamber of claim 5, wherein the interferometer endpoint detection system further comprises a computer for calculating at least a portion of the waveform spectra of the reflected light beam.

15. (Original) The chamber of claim 14, wherein the computer is configured to compare the waveform spectra of the reflected light beam with a stored characteristic waveform spectra pattern.

16. (Original) A photomask etch chamber, comprising:

a substrate support member disposed inside the chamber, wherein the substrate support member is configured to support a photomask substrate; and

an interferometer endpoint detection system disposed through a peripheral region of the substrate support member.

17. (Original) The chamber of claim 16, wherein the interferometer endpoint detection system is disposed directly below a corner region of the photomask substrate.

18. (Original) The chamber of claim 16, wherein the photomask substrate is about 6 inches wide and about 6 inches long and the interferometer endpoint detection system is disposed about 2.8 inches from a horizontal center line and about 2.8 inches from a vertical center line of the photomask substrate.

19. (Original) The chamber of claim 16, wherein the interferometer endpoint detection system is disposed directly below a peripheral region of the photomask substrate.

20. (Original) The chamber of claim 16, wherein the interferometer endpoint detection system is configured to detect a peripheral bottom region of the photomask substrate.

21. (Original) The chamber of claim 16, wherein the interferometer endpoint detection system is configured to detect one or more test patterns disposed on a peripheral region of the photomask substrate.

22. (Original) The chamber of claim 16, wherein the interferometer endpoint detection system is configured to detect one or more test patterns disposed on a corner region of the photomask substrate.

23. (New) A method of determining the endpoint of an etching process of a photomask substrate within a photomask etch chamber, comprising:

emitting a light beam;

illuminating one or more test patterns disposed on the photomask substrate with the light beam;

measuring the intensity of a reflected light beam, which is reflected from the one or more test patterns.

24. (New) The method of claim 23, wherein the one or more test patterns is located at a peripheral region of the photomask substrate.

25. (New) The method of claim 23, wherein the one or more test patterns is illuminated through a peripheral portion of a ceiling disposed on the photomask etch chamber.

26. (New) The method of claim 23, wherein the one or more testpatterns is illuminated on the test pattern through a peripheral portion of a substrate support member disposed inside the photomask etch chamber.

27. (New) The method of claim 23, wherein the measured intensity is an interference intensity.